



April 2015



FDB082N15A N-Channel PowerTrench[®] MOSFET 150 V, 117 A, 8.2 mΩ

Features

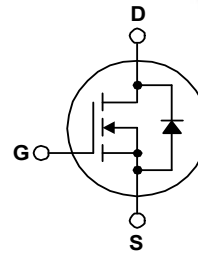
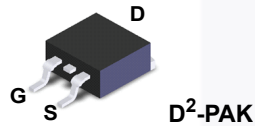
- $R_{DS(on)} = 6.7 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 75 \text{ A}$
- Fast Switching Speed
- Low Gate Charge, $Q_G = 64.5 \text{ nC}$ (Typ.)
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies
- Micro Solar Inverter



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDB082N15A	Unit
V_{DSS}	Drain to Source Voltage	150	V
V_{GSS}	Gate to Source Voltage	- DC	± 20
		- AC ($f > 1 \text{ Hz}$)	± 30
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$, Silicon Limited)	117
		- Continuous ($T_C = 100^\circ\text{C}$, Silicon Limited)	83
I_{DM}	Drain Current	- Pulsed (Note 1)	468
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	542
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	294
		- Derate Above 25°C	1.96
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDB082N15A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.51	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

FDB082N15A — N-Channel PowerTrench[®] MOSFET

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB082N15A	FDB082N15A	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}, T_C = 25^\circ\text{C}$	150	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	0.08	-	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120 \text{V}, V_{GS} = 0 \text{V}$	-	-	1	μA
		$V_{DS} = 120 \text{V}, T_C = 150^\circ\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{V}, V_{DS} = 0 \text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{V}, I_D = 75 \text{A}$	-	6.7	8.20	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{V}, I_D = 75 \text{A}$	-	139	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25 \text{V}, V_{GS} = 0 \text{V}, f = 1 \text{MHz}$	-	4645	6040	pF
C_{oss}	Output Capacitance		-	1445	1880	pF
C_{rss}	Reverse Transfer Capacitance		-	100	-	pF
C_{iss}	Input Capacitance	$V_{DS} = 75 \text{V}, V_{GS} = 0 \text{V}, f = 1 \text{MHz}$	-	4570	6040	pF
C_{oss}	Output Capacitance		-	460	1880	pF
C_{rss}	Reverse Transfer Capacitance		-	20	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 120 \text{V}, I_D = 75 \text{A}, V_{GS} = 10 \text{V}$	-	64.5	84	nC
Q_{gs}	Gate to Source Gate Charge		-	19.1	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	8.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note4)	-	13.5	-
ESR	Equivalent Series Resistance (G-S)	$f = 1 \text{MHz}$	-	2.5	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75 \text{V}, I_D = 75 \text{A}, V_{GS} = 10 \text{V}, R_G = 4.7 \Omega$	-	22	54	ns
t_r	Turn-On Rise Time		-	58	126	ns
$t_{d(off)}$	Turn-Off Delay Time		-	61	132	ns
t_f	Turn-Off Fall Time		(Note4)	-	26	62

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	117	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	468	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{V}, I_{SD} = 75 \text{A}$	-	-	1.25	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{V}, I_{SD} = 75 \text{A}, di_F/dt = 100 \text{A}/\mu\text{s}$	-	96	-	ns
Q_{rr}	Reverse Recovery Charge		-	268	-	nC

Notes:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. Starting $T_J = 25^\circ\text{C}$, $L = 3 \text{mH}$, $I_{SD} = 19 \text{A}$.
3. $I_{SD} \leq 75 \text{A}$, $di/dt \leq 200 \text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

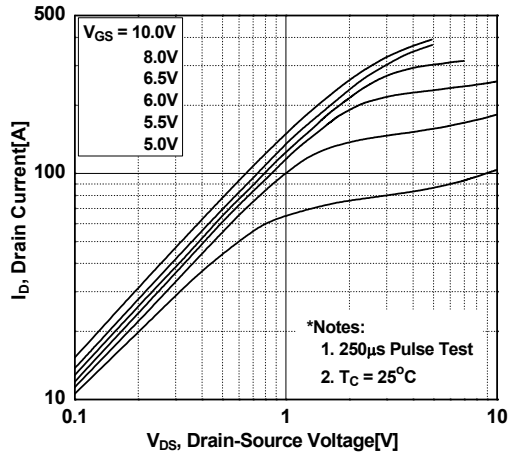


Figure 2. Transfer Characteristics

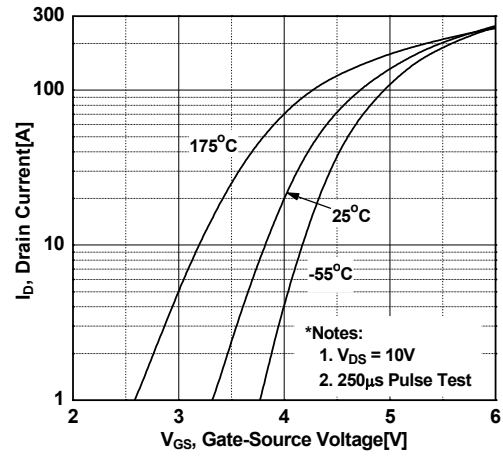


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

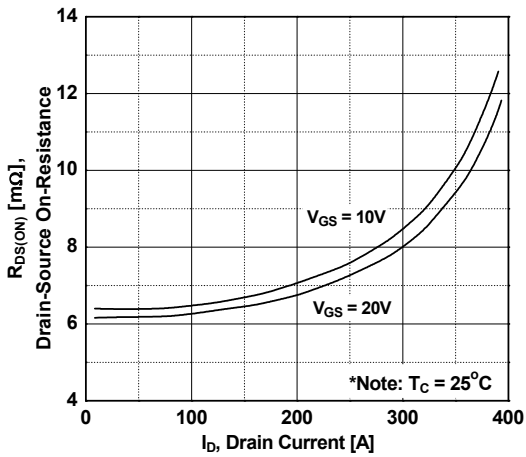


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

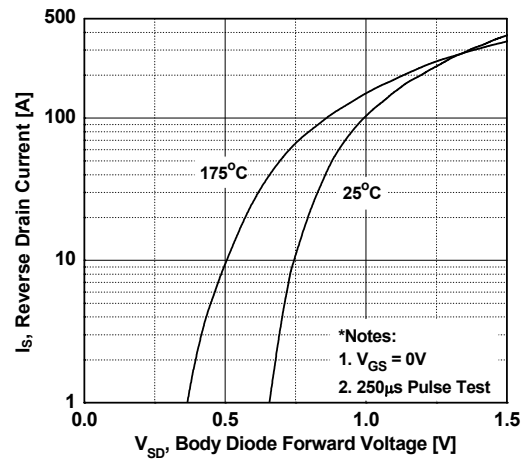


Figure 5. Capacitance Characteristics

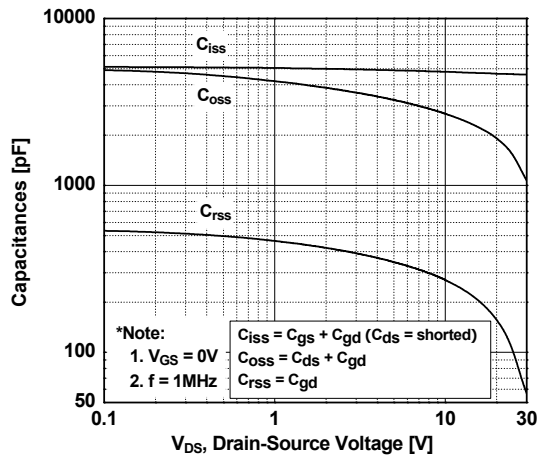
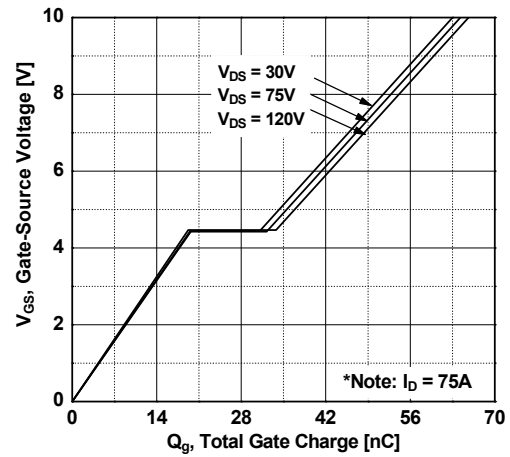


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

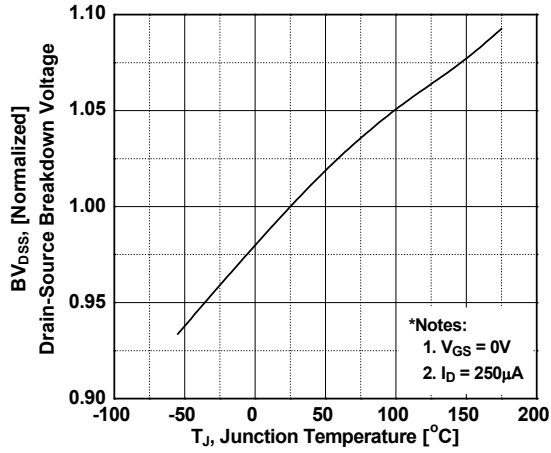


Figure 8. On-Resistance Variation vs. Temperature

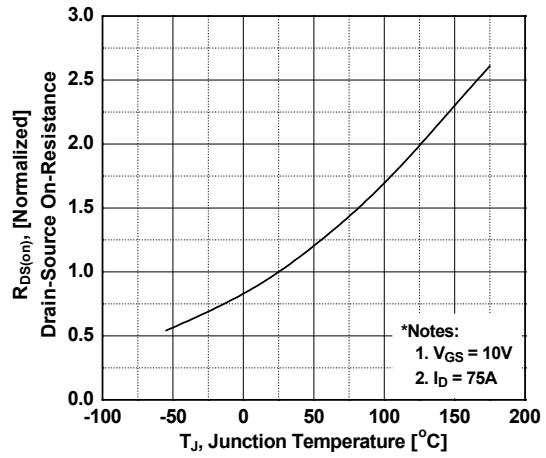


Figure 9. Maximum Safe Operating Area

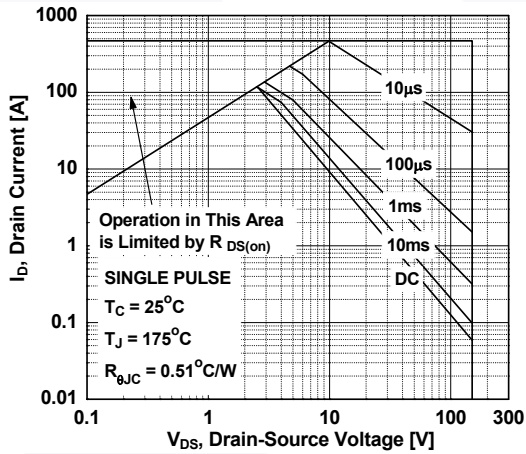


Figure 10. Maximum Drain Current vs. Case Temperature

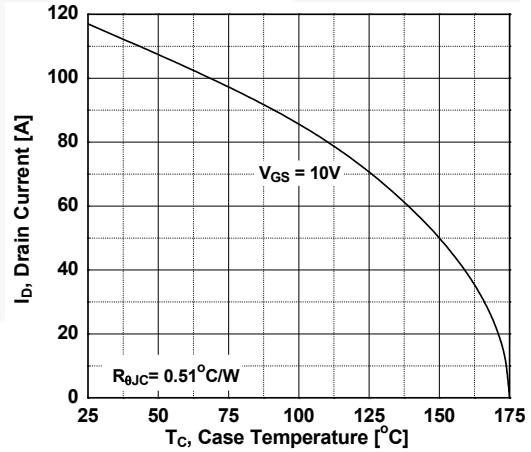
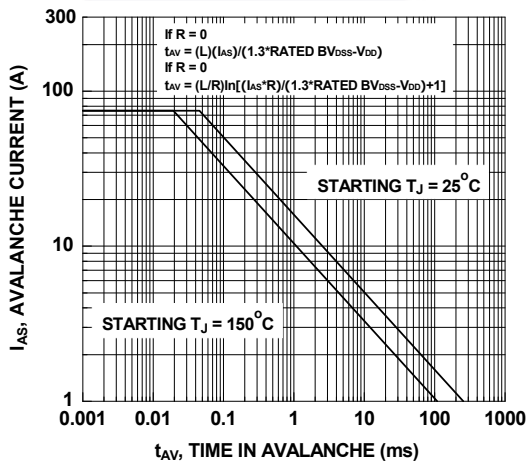
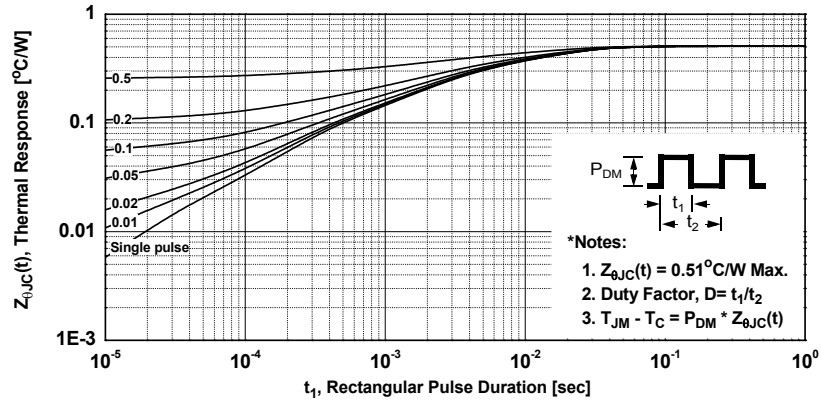


Figure 11. Unclamped Inductive Switching Capability



Typical Performance Characteristics

Figure 12. Transient Thermal Response Curve



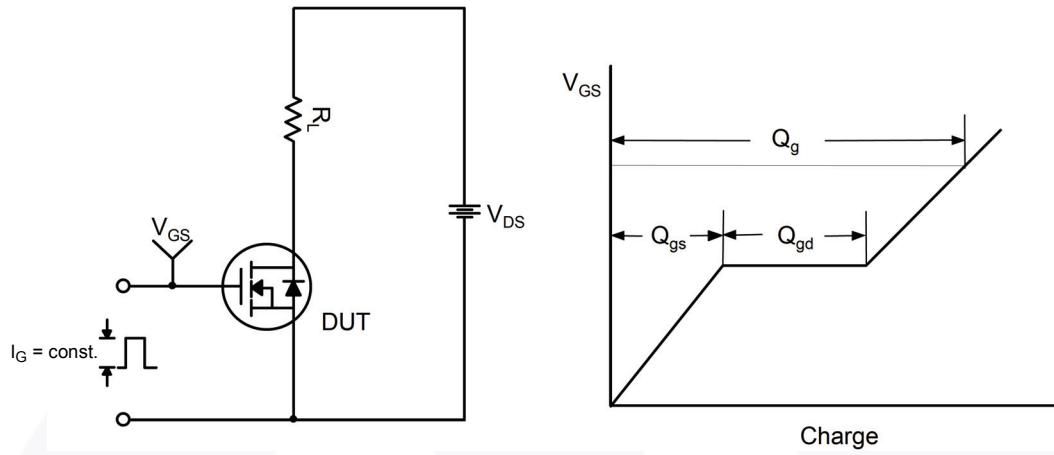


Figure 13. Gate Charge Test Circuit & Waveform

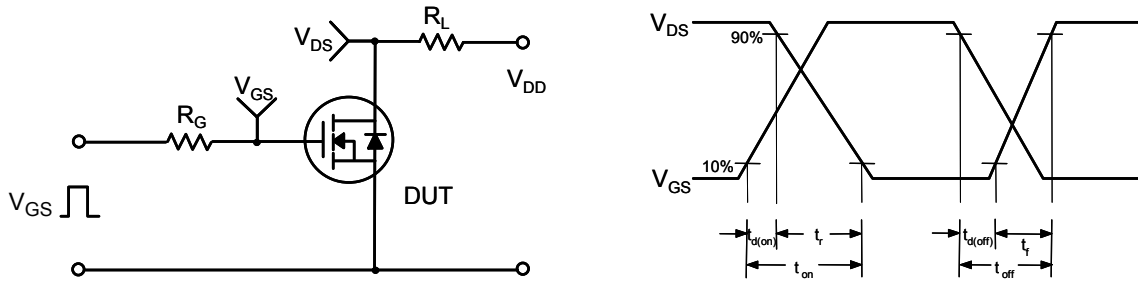


Figure 14. Resistive Switching Test Circuit & Waveforms

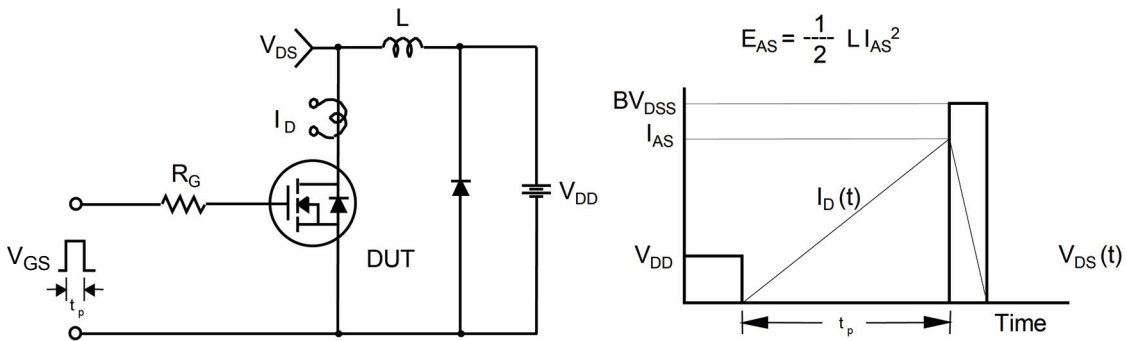


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

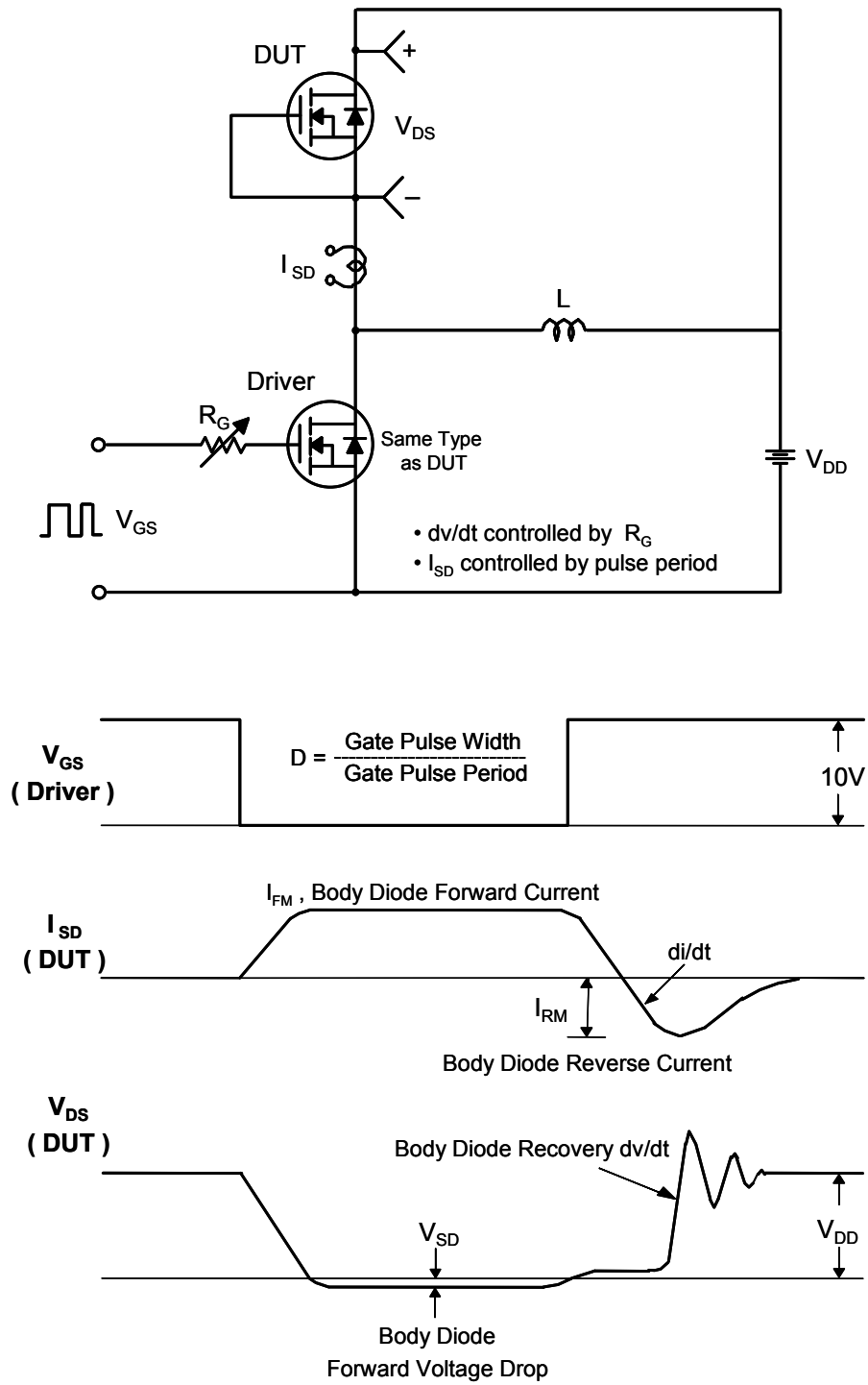
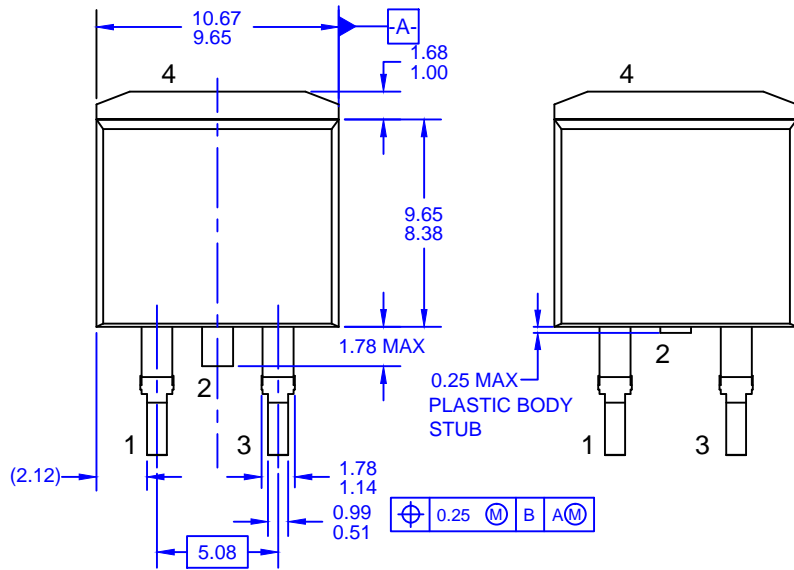
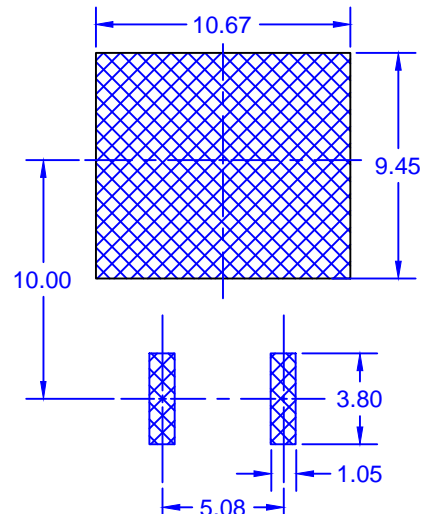


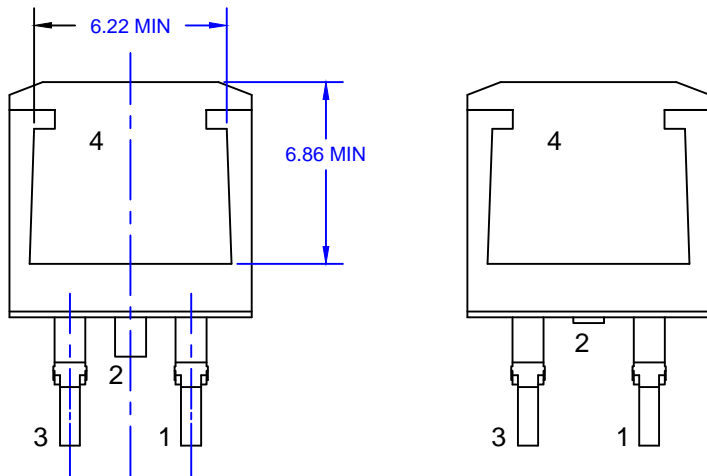
Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms



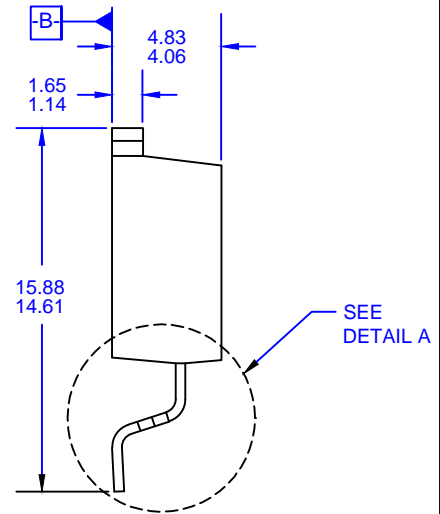
FRONT VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



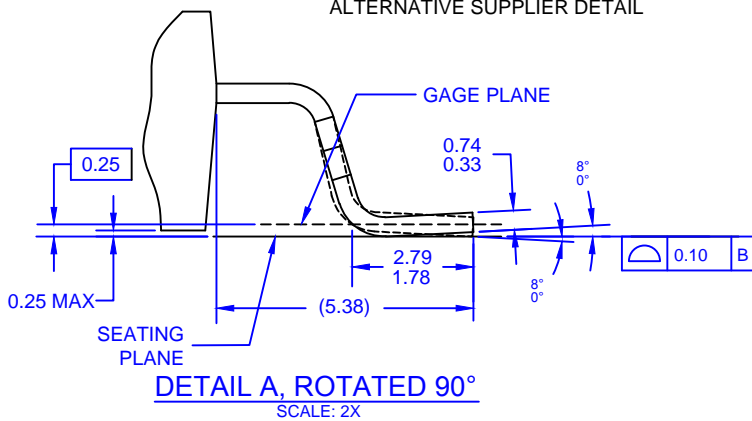
LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL



BACK VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



SEE
DETAIL A



DETAIL A, ROTATED 90°
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) REFERENCE JEDEC, TO-263, VARIATION AB.
- C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
- D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
- E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
- F) FILENAME: TO263A02REV8



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